

TO STEP 116 IN FIG. 1B

FIG. 1A

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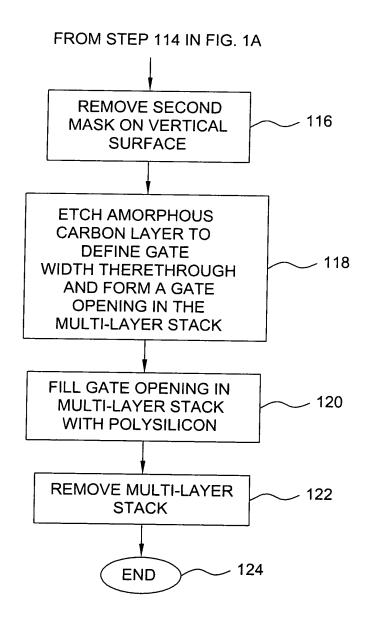


FIG. 1B

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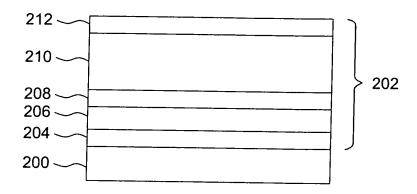


FIG. 2A

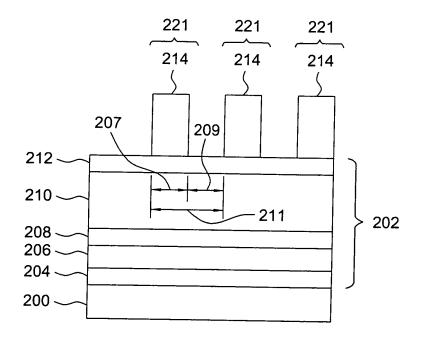


FIG. 2B

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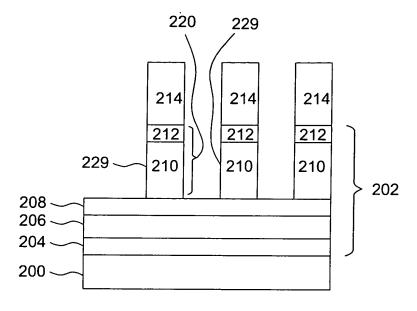


FIG. 2C

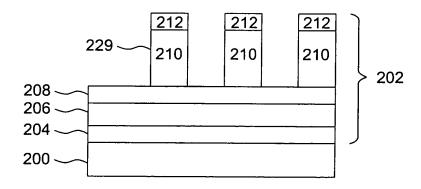


FIG. 2D

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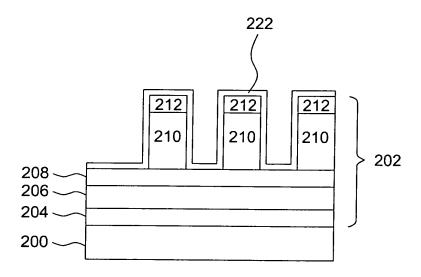


FIG. 2E

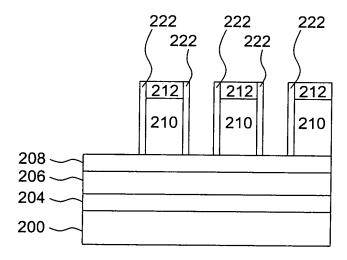


FIG. 2F

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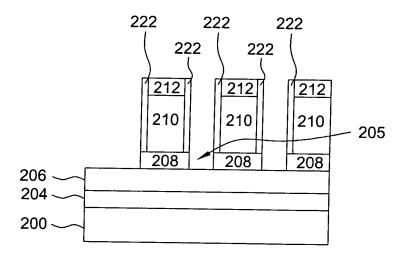


FIG. 2G

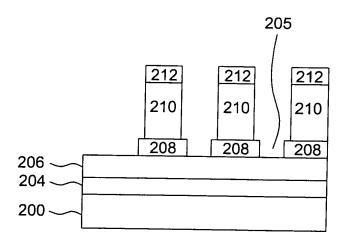


FIG. 2H

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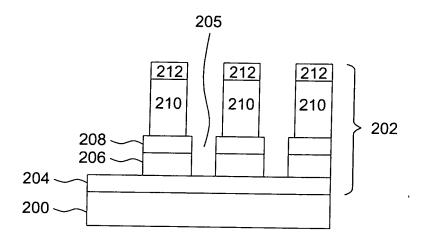


FIG. 21

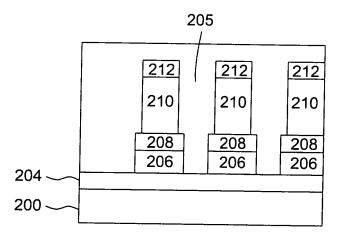


FIG. 2J

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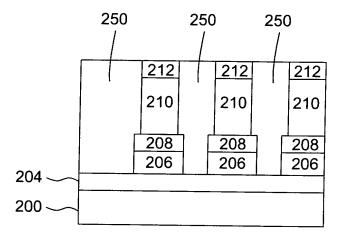


FIG. 2K

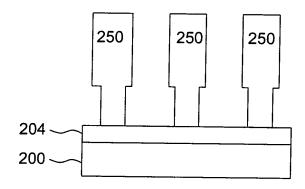


FIG. 2L

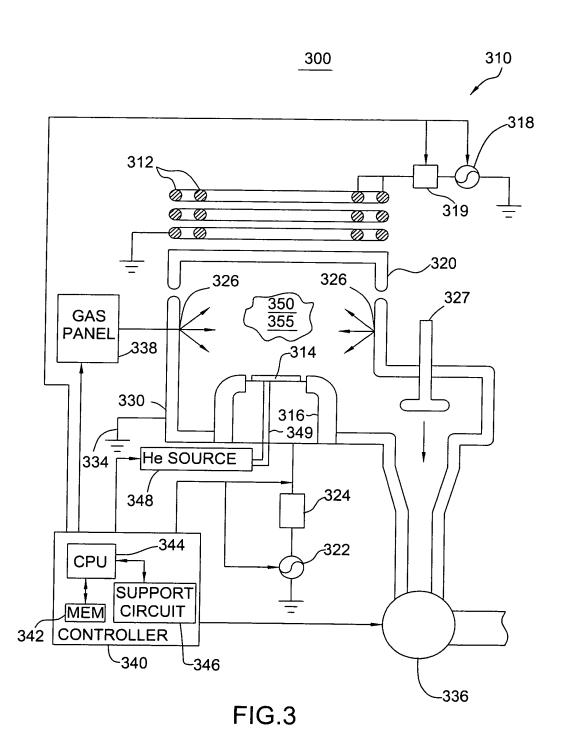
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